Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
60V	11mΩ @ V_{GS} = 10V	10.4A
	14mΩ @ V_{GS} = 4.5V	9.3A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- High Frequency Switching
- Synchronous Rectification
- DC-DC Converters

Features and Benefits

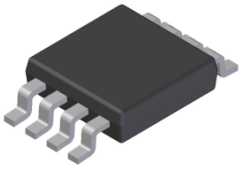
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Mechanical Data

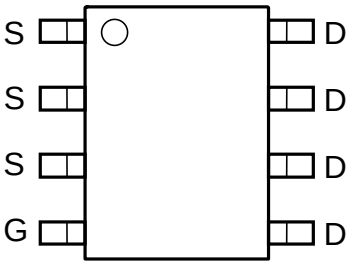
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.074 grams (Approximate)

ESD PROTECTED

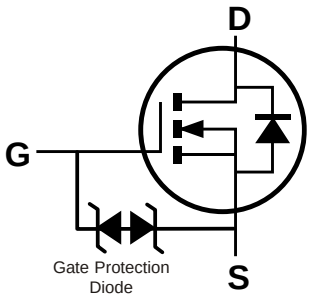
SO-8



Top View



Top View
Pin-Out



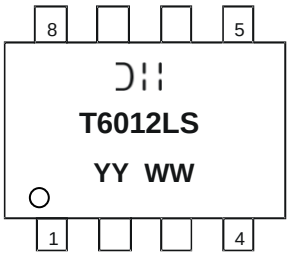
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6012LSS-13	SO-8	2,500/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



= Manufacturer's Marking
T6012LS = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 20 = 2020)
WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	10.4 8.4	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	10	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	65	A
Avalanche Current, L = 0.3mH			I_{AS}	15.8	A
Avalanche Energy, L = 0.3mH			E_{AS}	37.5	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	106	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.84	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	68	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	9.2	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 48V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.7	—	2	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	8.4	11	mΩ	V_{GS} = 10V, I_D = 10A
		—	11.5	14		V_{GS} = 4.5V, I_D = 5A
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	V_{GS} = 0V, I_S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1522	—	pF	V_{DS} = 30V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	352	—		
Reverse Transfer Capacitance	C_{rss}	—	27.5	—		
Gate Resistance	R_g	—	1.4	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	10.7	—	nC	V_{DS} = 30V, I_D = 10A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	22.2	—		
Gate-Source Charge	Q_{gs}	—	3.3	—		
Gate-Drain Charge	Q_{gd}	—	4.2	—		
Turn-On Delay Time	$t_{D(ON)}$	—	4.4	—	ns	V_{GS} = 10V, V_{DS} = 30V, R_G = 6Ω, I_D = 10A
Turn-On Rise Time	t_R	—	6.7	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	25.5	—		
Turn-Off Fall Time	t_F	—	12.5	—		
Body Diode Reverse Recovery Time	t_{RR}	—	25.8	—	ns	I_F = 10A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	15.1	—	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

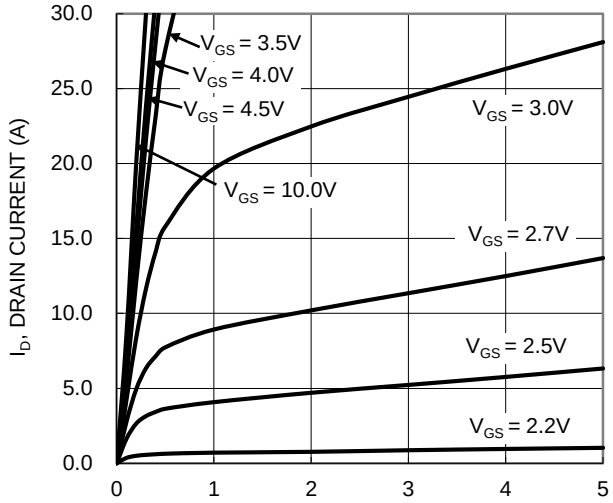


Figure 1.Typical Output Characteristic

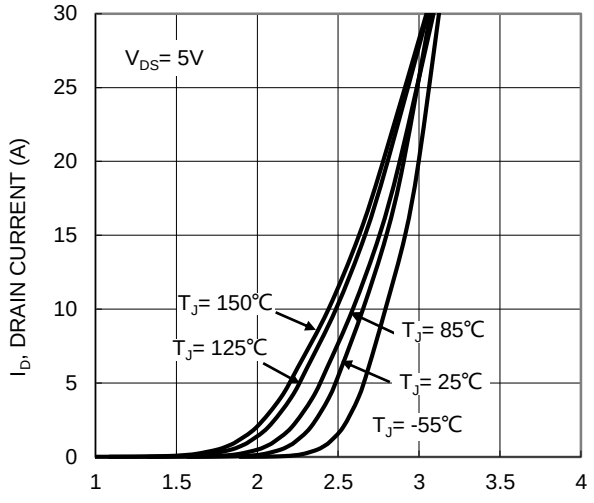


Figure 2. Typical Transfer Characteristic

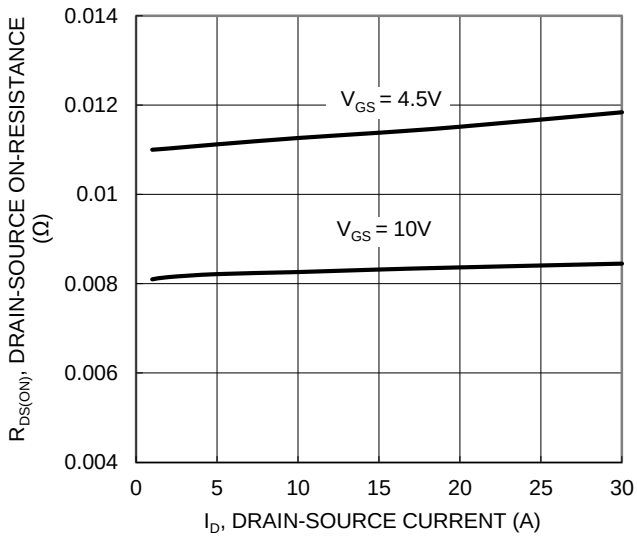


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

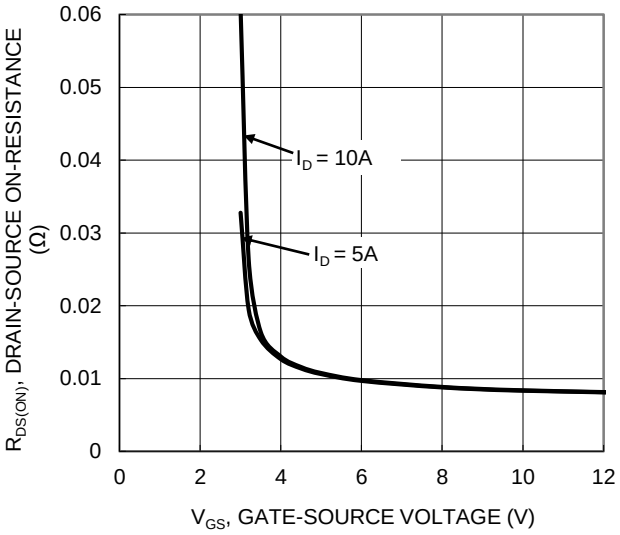


Figure 4. Typical Transfer Characteristic

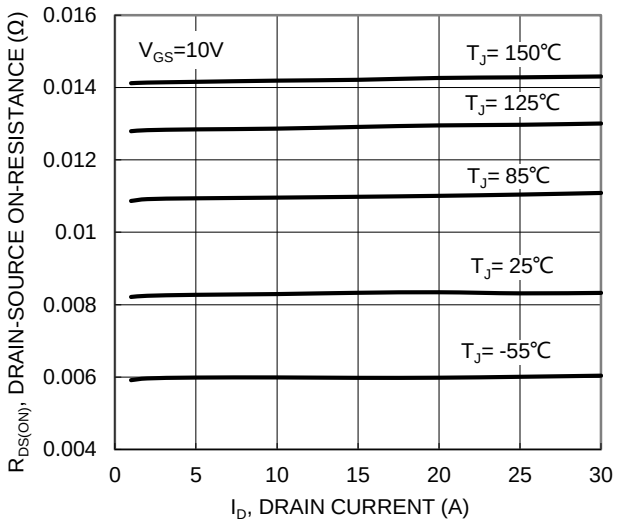


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

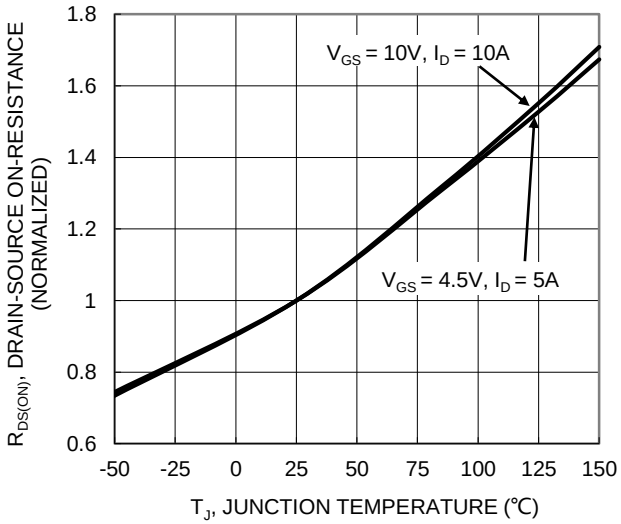


Figure 6. On-Resistance Variation with Temperature

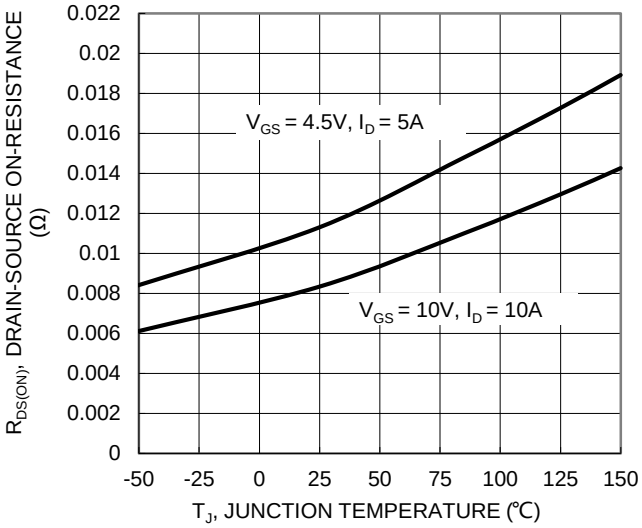


Figure 7. On-Resistance Variation with Temperature

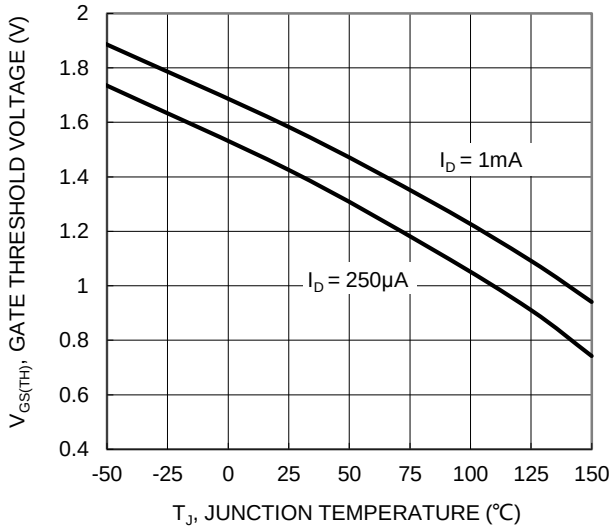


Figure 8. Gate Threshold Variation vs. JunctionTemperature

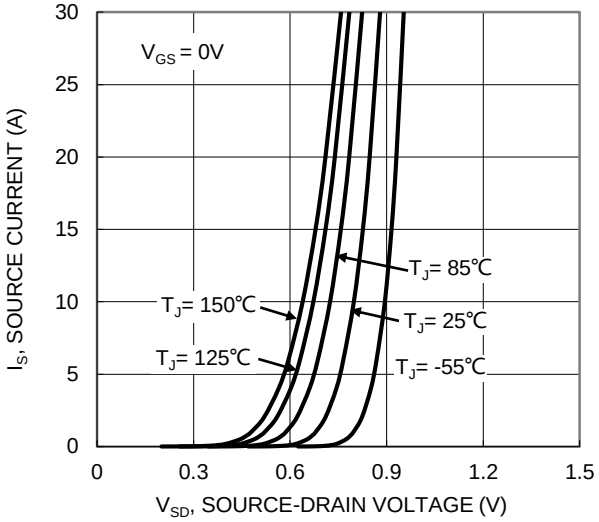


Figure 9. Diode Forward Voltage vs. Current

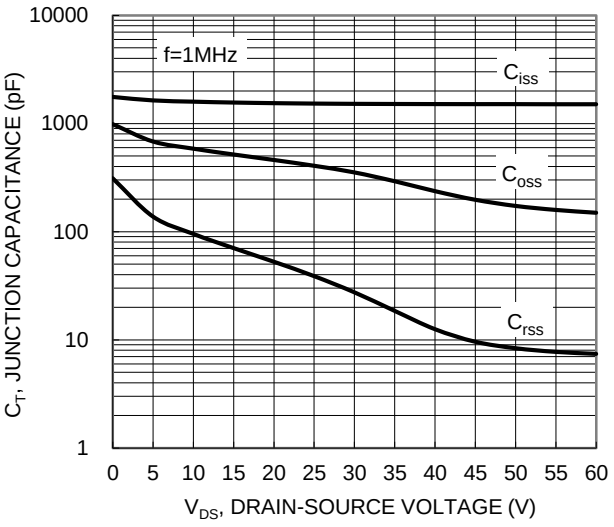


Figure 10. Typical Junction Capacitance

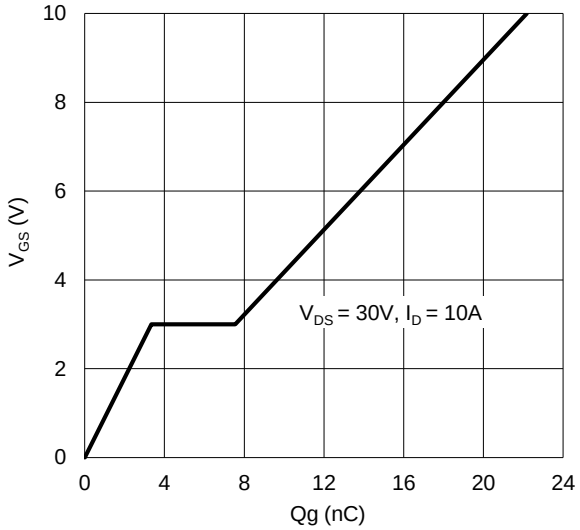


Figure 11. Gate Charge

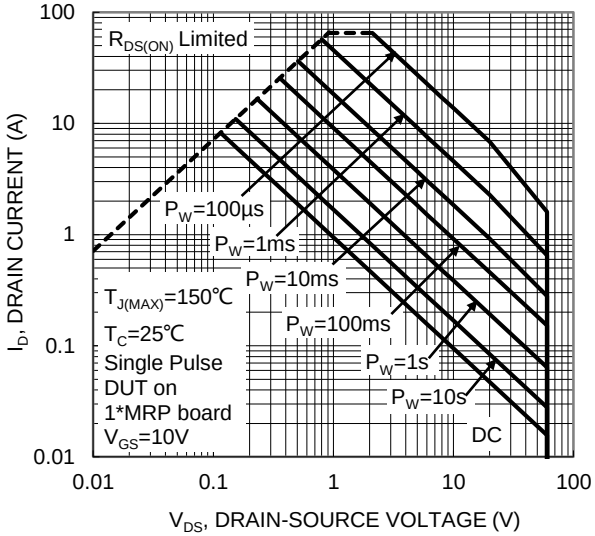


Figure 12. SOA, Safe Operation Area

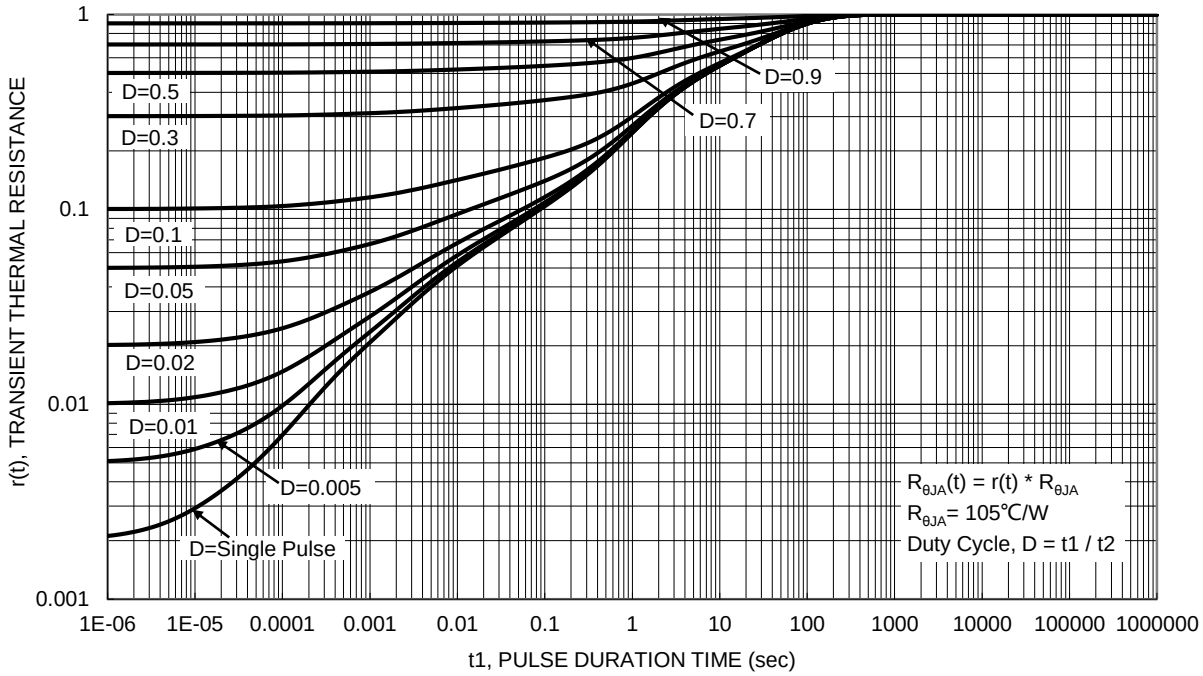


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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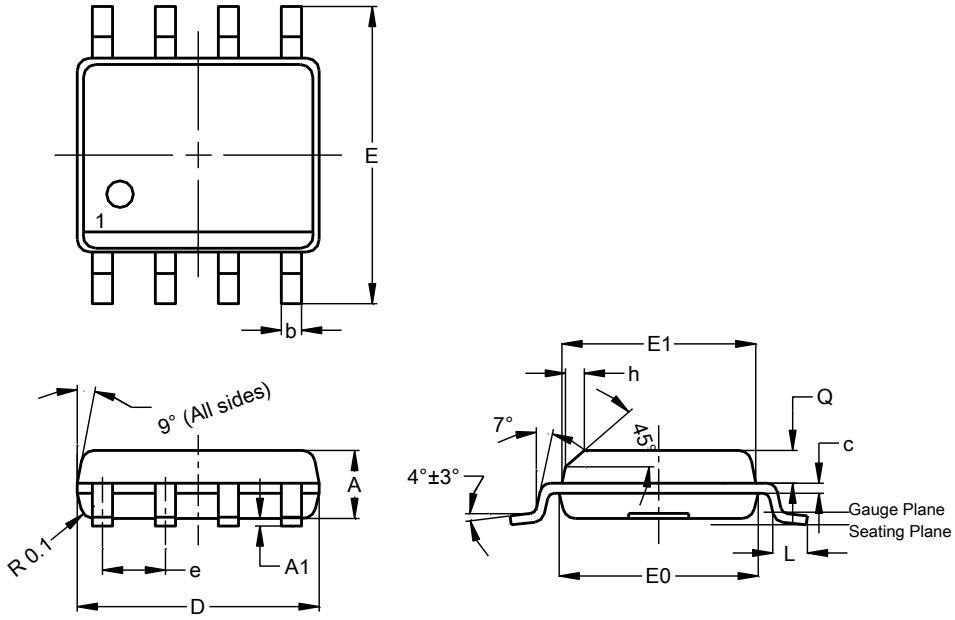
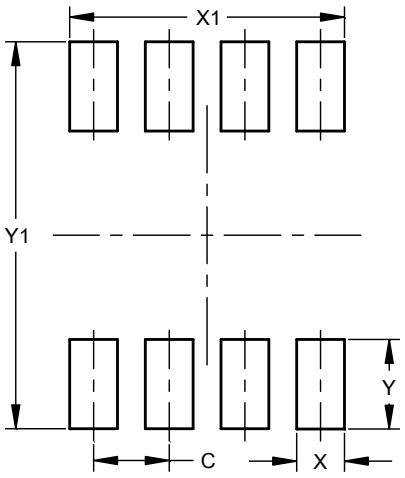


SO-8			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	--	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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